74LV132-Q100

Quad 2-input NAND Schmitt trigger

Rev. 1 — 11 November 2013 Product data sheet

1. General description

The 74LV132-Q100 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC132-Q100 and 74HCT132-Q100.

The 74LV132-Q100 contains four 2-input NAND gates which accept standard input signals. These gates are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The gate switches at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Applications

- Wave and pulse shapers for highly noisy environments
- Astable multivibrators
- Monostable multivibrators

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV132D-Q100	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV132PW-Q100	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV132BQ-Q100	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

5. Functional diagram

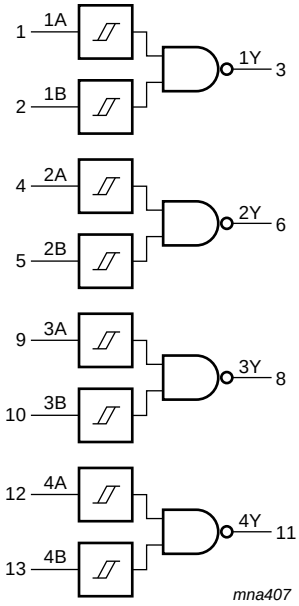


Fig 1. Logic symbol

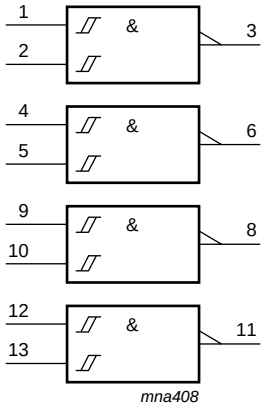


Fig 2. IEC logic symbol

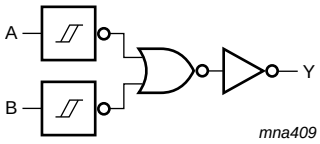


Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning

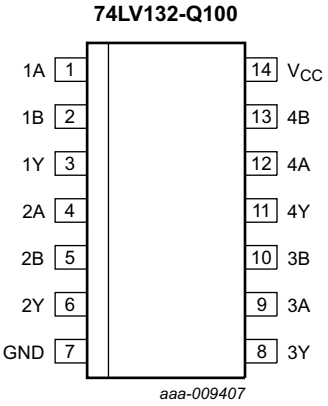
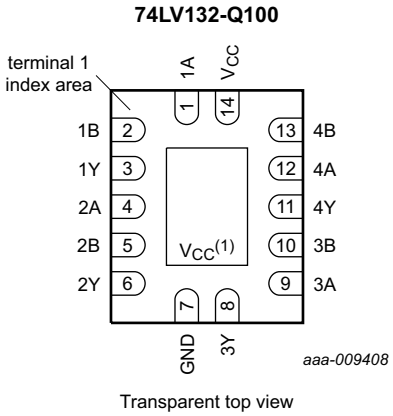


Fig 4. Pin configuration SO14 and TSSOP14



Transparent top view

(1) The die substrate is attached to the exposed die pad using conductive die attach material. It cannot be used as a supply pin or input.

Fig 5. Pin configuration DHVQFN14

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V_{CC}	14	supply voltage

7. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input		Output
nA	**nB**	**nY**
L	L	H
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±50	mA
I_O	output current	$V_O = –0.5$ V to $(V_{CC} + 0.5$ V)		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = –40$ °C to +125 °C				
	SO14 package		[2]	-	500	mW
	TSSOP14 package		[3]	-	500	mW
	DHVQFN14 package		[4]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CC}	supply voltage		[1]	1.0	3.3	5.5	V
V_I	input voltage			0	-	V_{CC}	V
V_O	output voltage			0	-	V_{CC}	V
T_{amb}	ambient temperature			−40	+25	+125	°C

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V. LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

10. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}						
		I_O = −100 μA; V_{CC} = 1.2 V	-	1.2	-	-	-	V
		I_O = −100 μA; V_{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I_O = −100 μA; V_{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I_O = −100 μA; V_{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I_O = −100 μA; V_{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I_O = −6 mA; V_{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I_O = −12 mA; V_{CC} = 4.5 V	3.6	4.2	-	3.5	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}						
		I_O = 100 μA; V_{CC} = 1.2 V	-	0	-	-	-	V
		I_O = 100 μA; V_{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I_O = 100 μA; V_{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I_O = 100 μA; V_{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I_O = 100 μA; V_{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I_O = 6 mA; V_{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I_O = 12 mA; V_{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	1.0	-	1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	20.0	-	40	μA
ΔI_{CC}	additional supply current	per input; $V_I = V_{CC}$ − 0.6 V; V_{CC} = 2.7 V to 3.6 V	-	-	500	-	850	μA
C_I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; for test circuit, see Figure 7.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, nB to nY; see Figure 6	[2]						
		V_{CC} = 1.2 V		-	65	-	-	-	ns
		V_{CC} = 2.0 V		-	18	34	-	43	ns
		V_{CC} = 2.7 V		-	15	24	-	30	ns
		V_{CC} = 3.0 V to 3.6 V; C_L = 15 pF	[3]	-	10	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V	[3]	-	12	20	-	25	ns
		V_{CC} = 4.5 V to 5.5 V	[3]	-	9.0	14	-	17	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	24	-	-	-	pF

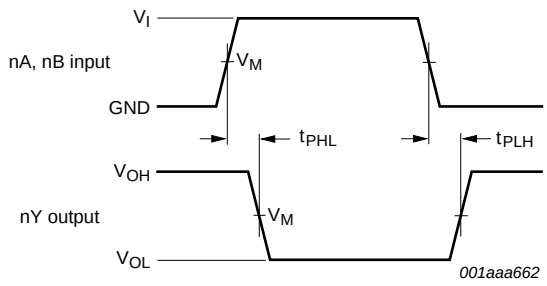
[1] All typical values are measured at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz, f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in V
N = number of inputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



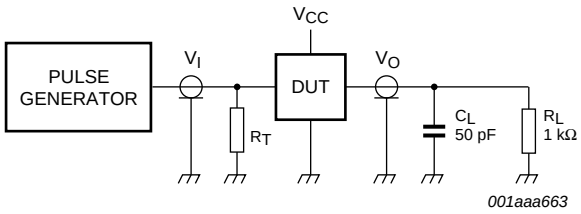
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig 7. Load circuit for switching times

Table 9. Test data

Supply voltage	Input	
V_{CC}	V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

13. Transfer characteristics

Table 10. Transfer characteristics

GND = 0 V; for test circuit, see Figure 7.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 6						
		V_{CC} = 1.2 V	-	0.70	-	-	-	V
		V_{CC} = 2.0 V	0.8	1.10	1.4	0.8	1.4	V
		V_{CC} = 2.7 V	1.0	1.45	2.0	1.0	2.0	V
		V_{CC} = 3.0 V	1.2	1.60	2.2	1.2	2.2	V
		V_{CC} = 3.6 V	1.5	1.95	2.4	1.5	2.4	V
		V_{CC} = 4.5 V	1.7	2.50	3.2	1.7	3.2	V
		V_{CC} = 5.5 V	2.1	3.00	3.9	2.1	3.9	V

Table 10. Transfer characteristics *…continued*

GND = 0 V; for test circuit, see Figure 7.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{T-}	negative-going threshold voltage	see Figure 6						
		V_{CC} = 1.2 V	-	0.34	-	-	-	V
		V_{CC} = 2.0 V	0.3	0.65	0.9	0.3	0.9	V
		V_{CC} = 2.7 V	0.4	0.90	1.4	0.4	1.4	V
		V_{CC} = 3.0 V	0.6	1.05	1.5	0.6	1.5	V
		V_{CC} = 3.6 V	0.8	1.30	1.8	0.8	1.8	V
		V_{CC} = 4.5 V	0.9	1.60	2.0	0.9	2.0	V
		V_{CC} = 5.5 V	1.2	2.00	2.6	1.2	2.6	V
V_H	hysteresis voltage	($V_{T+} - V_{T-}$); see Figure 6						
		V_{CC} = 1.2 V	-	0.3	-	-	-	V
		V_{CC} = 2.0 V	0.2	0.55	0.8	0.2	0.8	V
		V_{CC} = 2.7 V	0.3	0.60	1.1	0.3	1.1	V
		V_{CC} = 3.0 V	0.4	0.65	1.2	0.4	1.2	V
		V_{CC} = 3.6 V	0.4	0.70	1.2	0.4	1.2	V
		V_{CC} = 4.5 V	0.4	0.80	1.4	0.4	1.4	V
		V_{CC} = 5.5 V	0.6	1.00	1.5	0.6	1.5	V

[1] All typical values are measured at T_{amb} = 25 °C.

14. Waveforms transfer characteristics

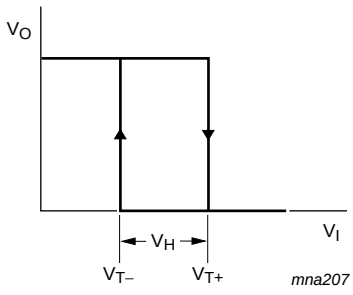
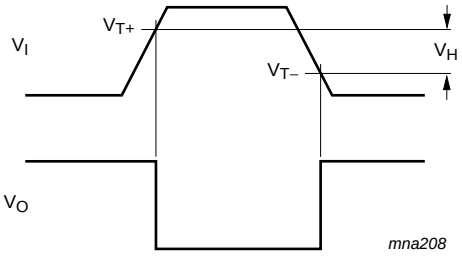
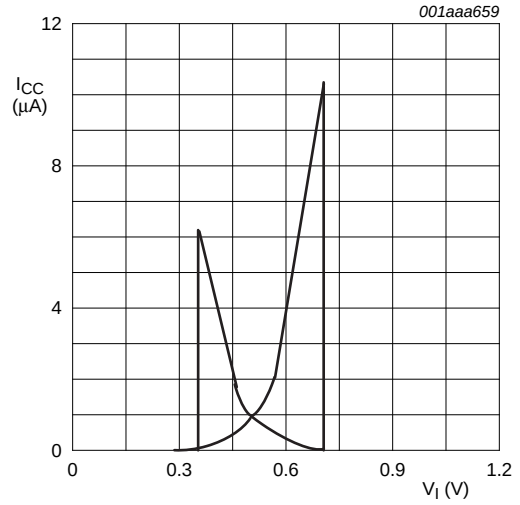


Fig 8. Transfer characteristic



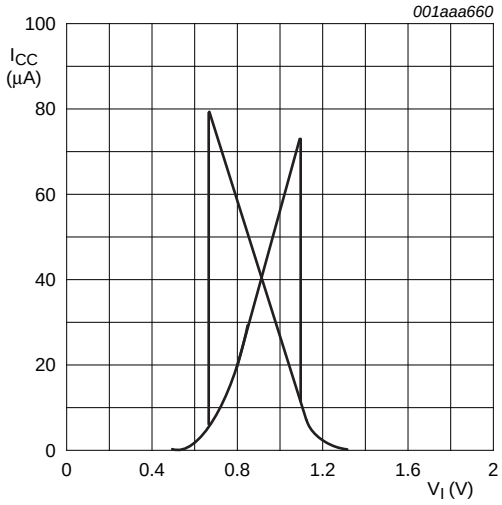
V_{T+} and V_{T-} limits at 70 % and 20 %.

Fig 9. Definition of V_{T+}, V_{T-} and V_H



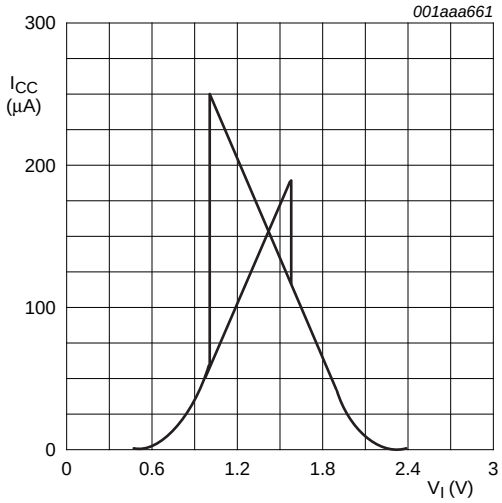
V_{CC} = 1.2 V.

Fig 10. Typical 74LV132-Q100 transfer characteristics



V_{CC} = 2.0 V.

Fig 11. Typical 74LV132-Q100 transfer characteristics

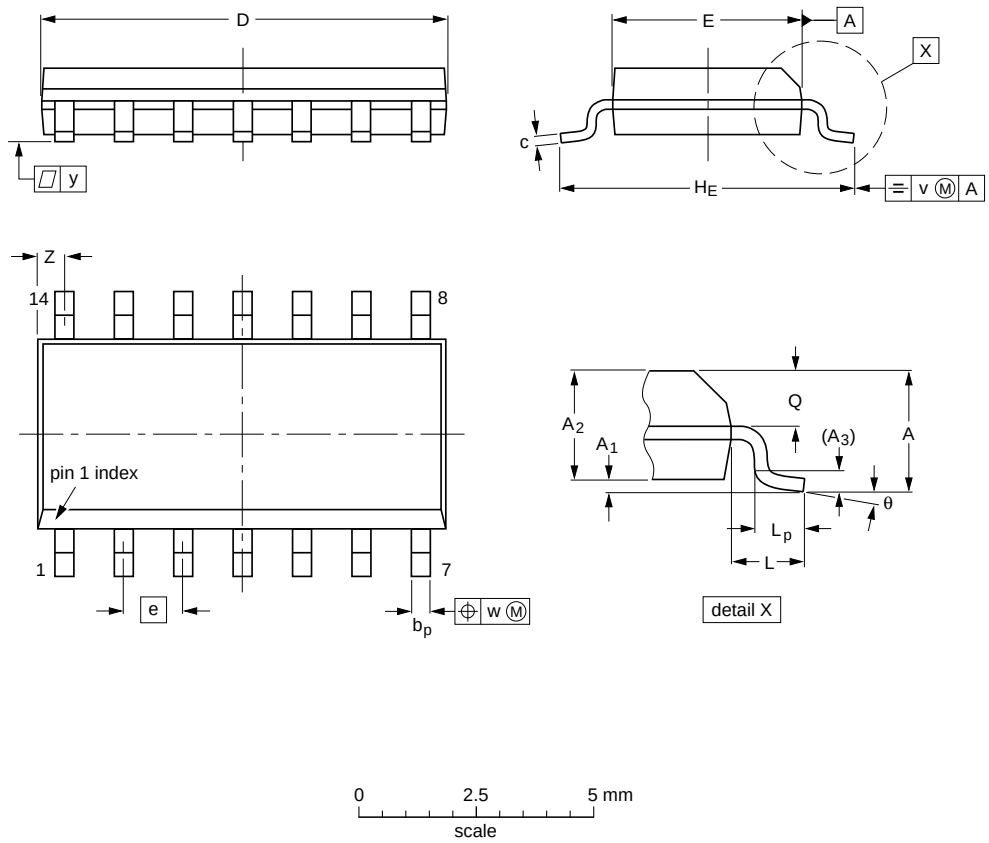


V_{CC} = 3.0 V.

Fig 12. Typical 74LV132-Q100 transfer characteristics

15. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

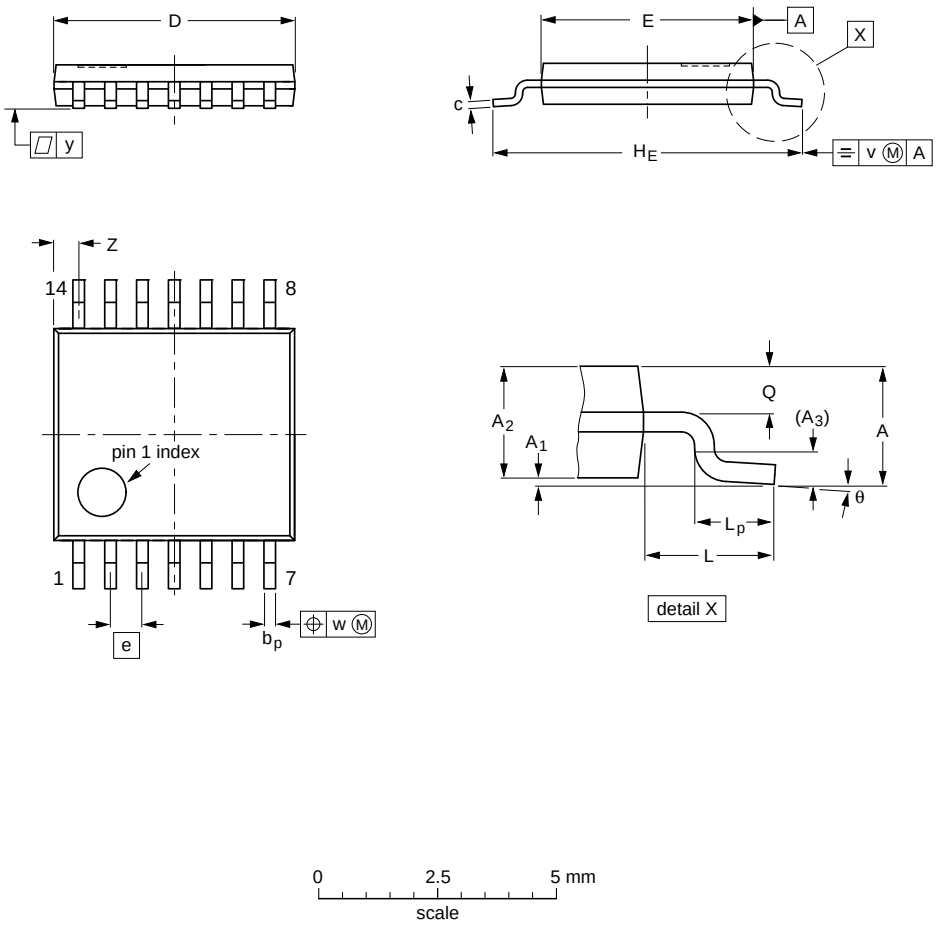
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 13. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm **SOT402-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8^o 0^o

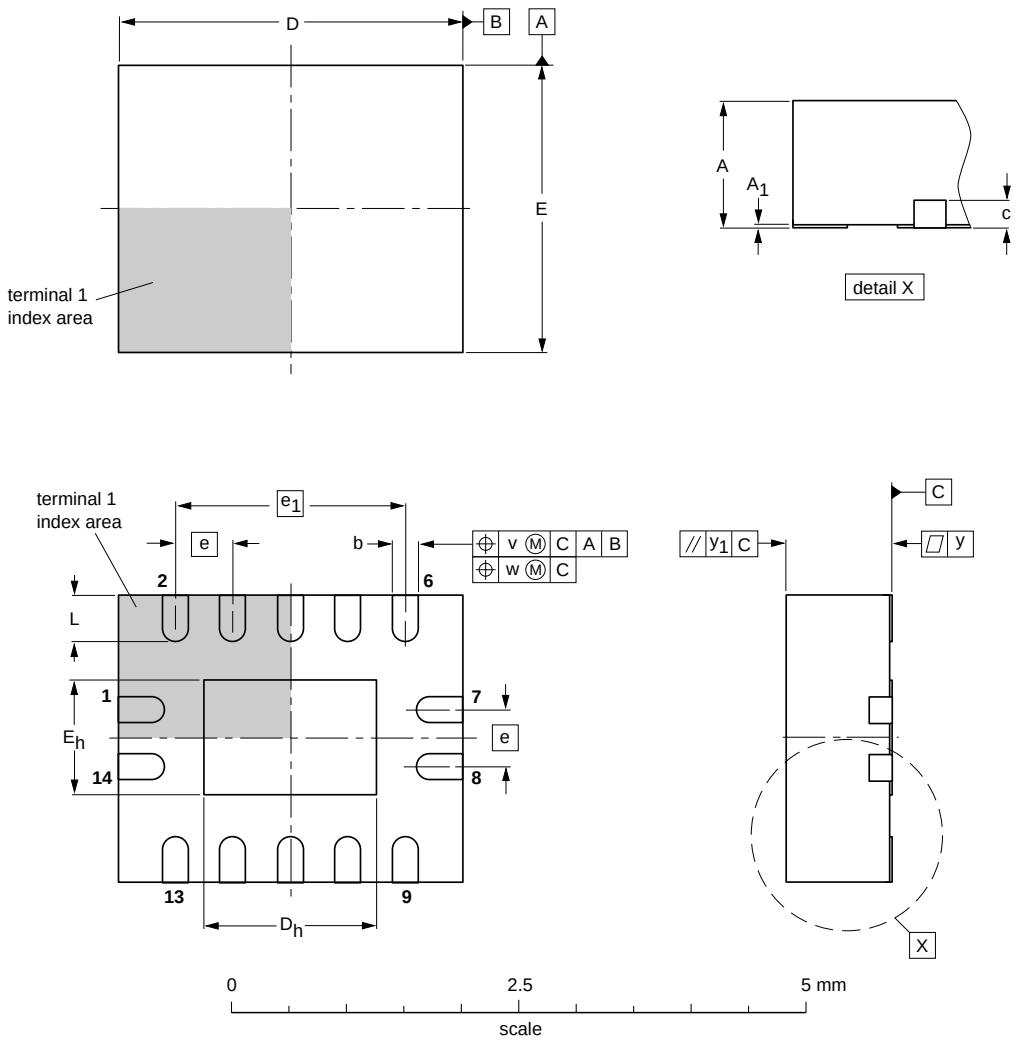
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT402-1		MO-153				~~99-12-27~~ 03-02-18

Fig 14. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm **SOT762-1**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max.	A_1	b	c	$D^{(1)}$	D_h	$E^{(1)}$	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.1 2.9	1.65 1.35	2.6 2.4	1.15 0.85	0.5	2	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT762-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 15. Package outline SOT762-1 (DHVQFN14)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV132_Q100 v.1	20131111	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

18.2 Definitions

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19. Contact information

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For sales office addresses, please send an email to: **salesaddresses@nxp.com**

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